

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

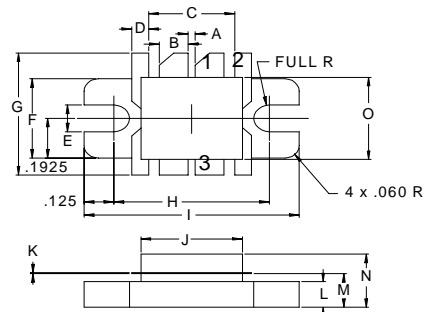
The **ASI VTV1250** is Designed for Television Band III Applications up to 225 MHz.

FEATURES:

- Common Emitter
- $P_G = 12$ dB at 125 W/225 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CBO}	65 V
V_{CEO}	33 V
V_{EBO}	3.5 V
P_{DISS}	150 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.8 °C/W

PACKAGE STYLE .400 8L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N	.280 / 7.11	
O	.395 / 10.03	.405 / 10.29

1 = COLLECTOR 2 = EMITTER 3 = BASE

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	33			V
BV_{CES}	$I_C = 100$ mA	65			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.0$ mA	20			---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz	---	65	---	pF
P_G	$V_{CC} = 28$ V $I_C = 300$ mA $f = 225$ MHz $P_{OUT} = 125$ W	12			Db
η_c		60	65		%
$VSRW_1$				3:1	---